

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
40V	4.3mΩ@10V	93A

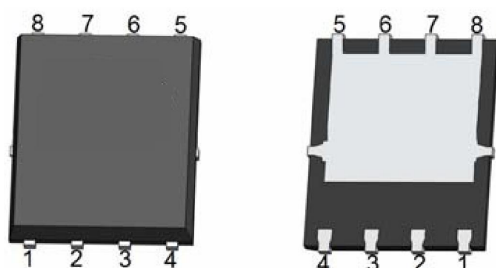
Feature

- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- Suffix "-Q1" for AEC-Q101

Application

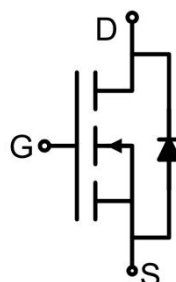
- DC-DC converter
- Ideal for high-frequency switching
- Synchronous rectification

Package

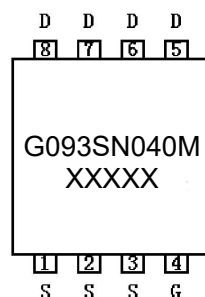


PDFN5*6-8L

Circuit diagram



Marking



Absolute maximum ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	93	A
Continuous Drain Current (T _c =100°C)	I _D (100°C)	58	A
Pulsed Drain Current	I _{DM}	372	A
Single Pulse Avalanche Energy ¹⁾	E _{AS}	163	mJ
Power Dissipation	P _D	60	W
Thermal Resistance Junction to Case	R _{θJC}	2.08	°C/W
Operating Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Electrical characteristics (T_c=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	40			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =40V, V _{GS} =0V			1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A		3.6	4.3	mΩ
Dynamic characteristics ²⁾						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, f =1MHz		1370		pF
Output Capacitance	C _{oss}			365		
Reverse Transfer Capacitance	C _{rss}			27		
Total Gate Charge	Q _g	V _{DS} =20V, V _{GS} =10V, I _D =20A		25		nC
Gate-Source Charge	Q _{gs}			7.5		
Gate-Drain Charge	Q _{gd}			6.2		
Turn-on delay time	t _{d(on)}	V _{DS} =20V, V _{GS} =10V, I _D =20A R _G =3Ω		10		nS
Turn-on rise time	t _r			45		
Turn-off delay time	t _{d(off)}			18		
Turn-off fall time	t _f			8		
Source-Drain Diode characteristics						
Diode Forward Current	I _S				93	A
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _S =20A			1.2	V
Reverse Recovery Time	T _{rr}	I _F =20A, di/dt =100A/μs		42		nS
Reverse Recovery Charge	Q _{rr}	T _J =25°C		29		nC

Notes:

1) EAS condition : T_J=25°C, V_{DD}=20V, V_G=10V, L=0.5mH, R_G=25Ω.

2) Guaranteed by design, not subject to production.

Typical Characteristics

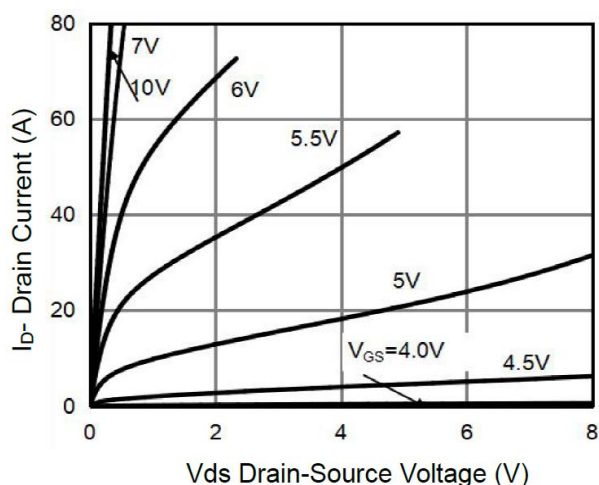


Figure 1 Output Characteristics

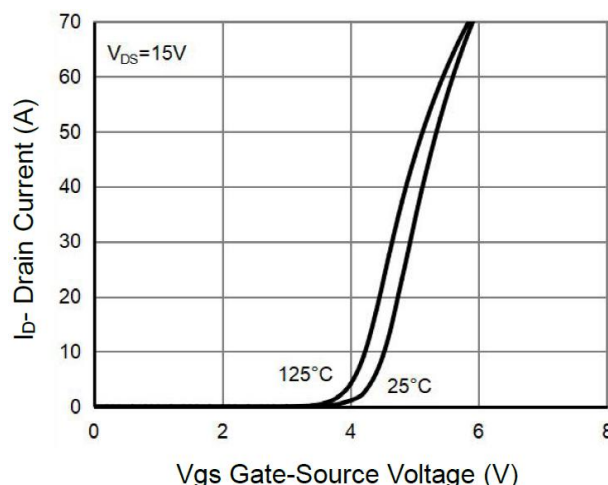


Figure 2 Transfer Characteristics

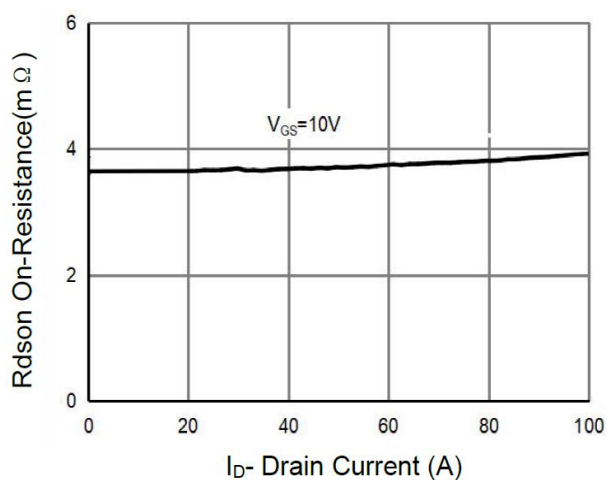


Figure 3 Rdson- Drain Current

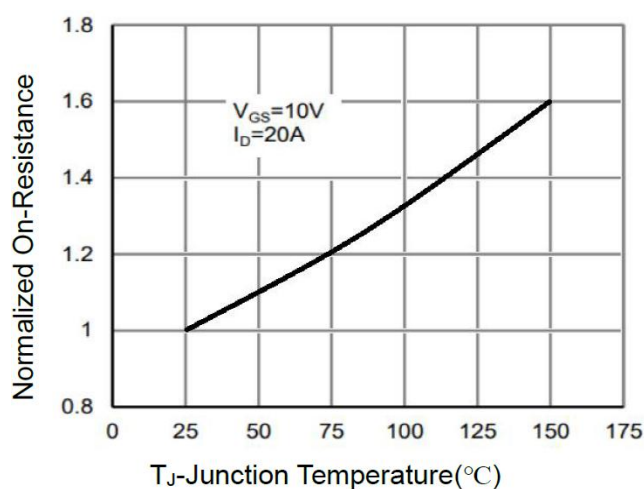


Figure 4 Rdson-Junction Temperature

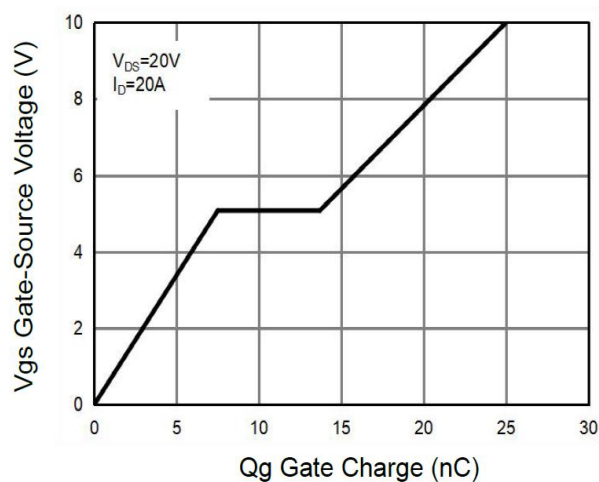


Figure 5 Gate Charge

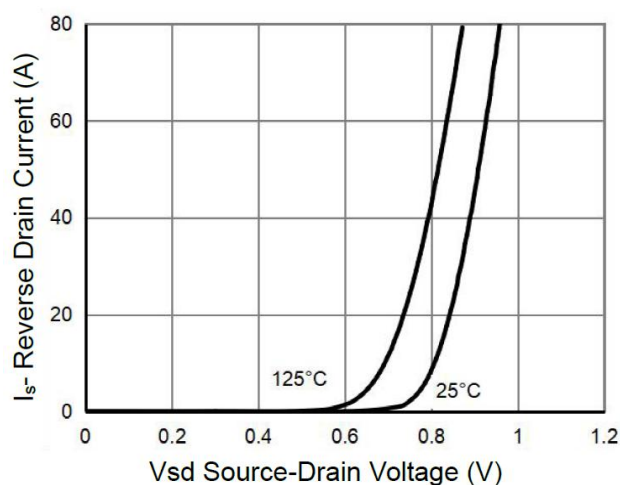


Figure 6 Source- Drain Diode Forward

Typical Characteristics

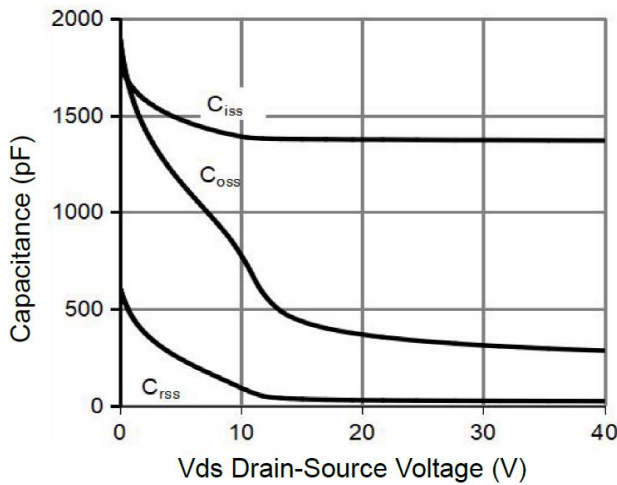


Figure 7 Capacitance vs Vds

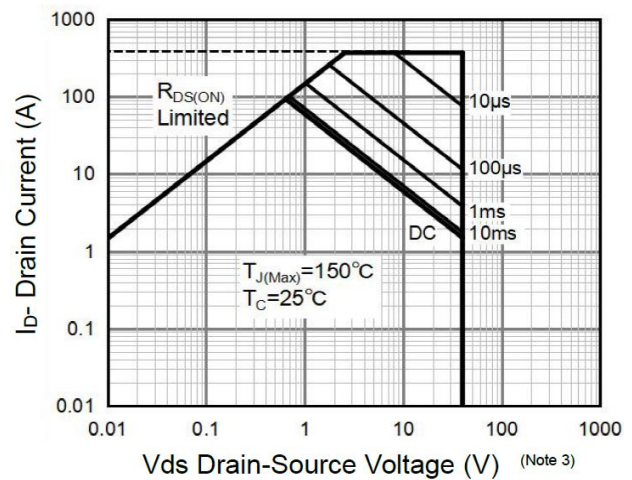


Figure 8 Safe Operation Area

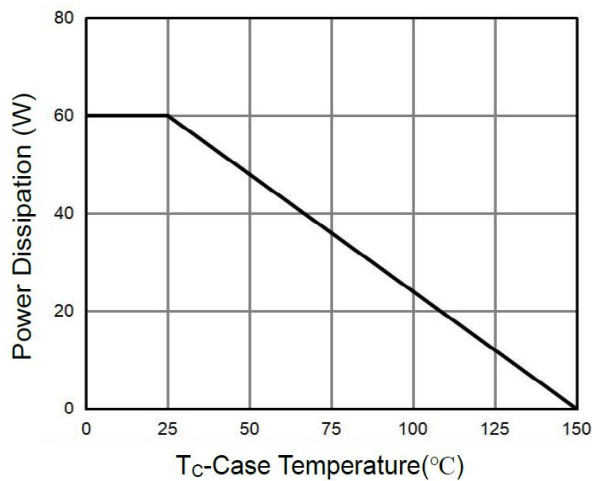


Figure 9 Power De-rating

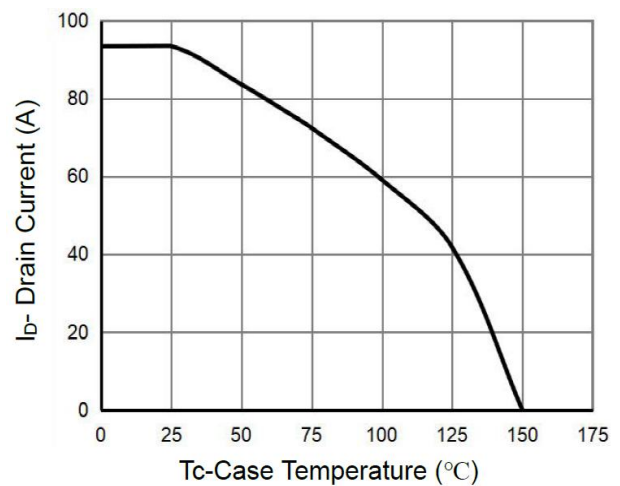


Figure 10 Current De-rating

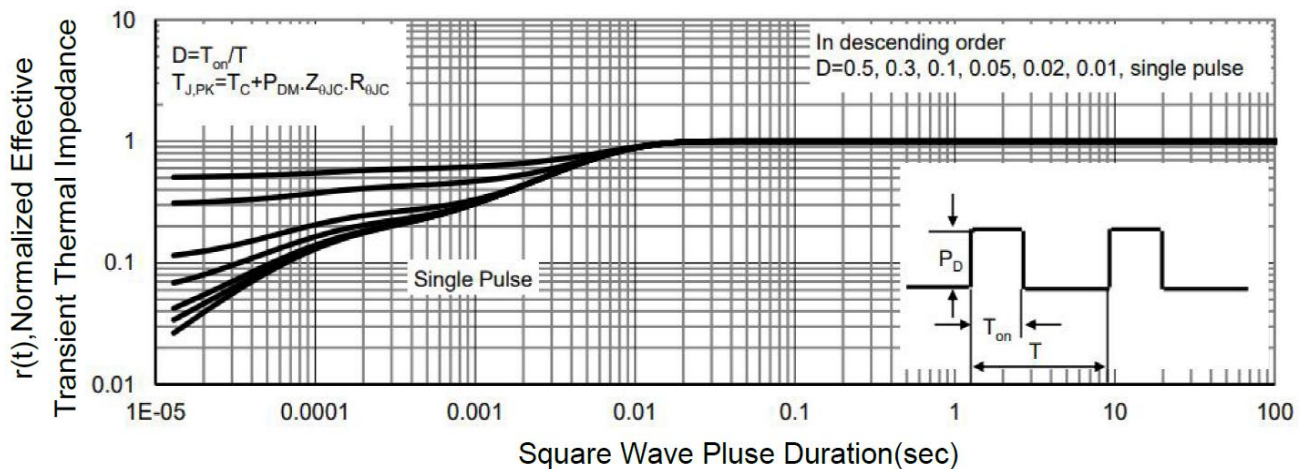
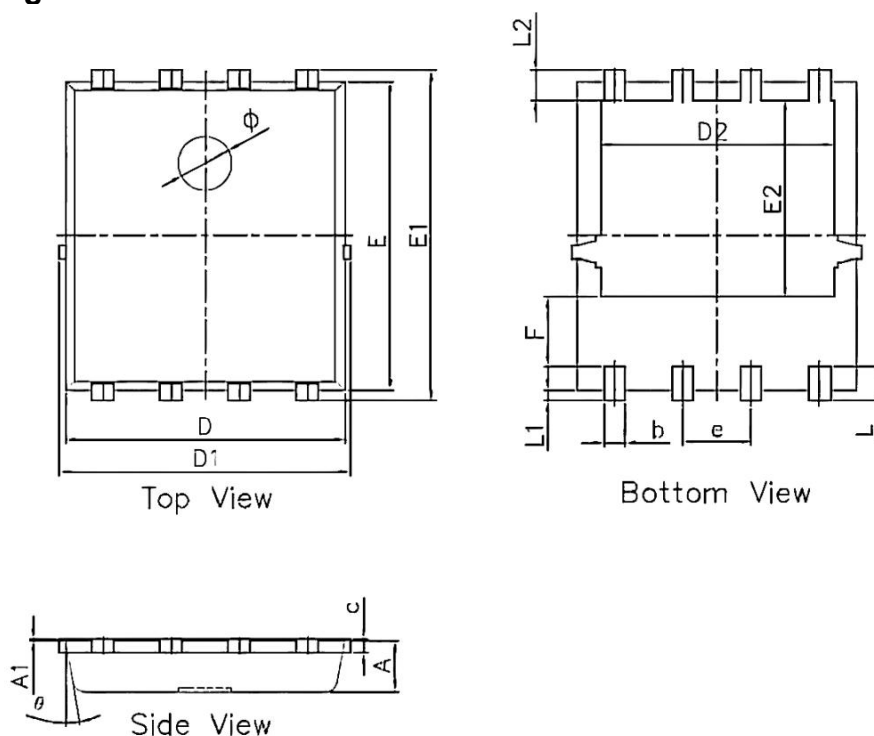


Figure 11 Normalized Maximum Transient Thermal Impedance

PDFN5*6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A1	0.000	0.005	0.000	0.000
b	0.350	0.500	0.014	0.020
c	0.200	0.300	0.008	0.012
D	5.100	5.300	0.201	0.209
D1	5.100	5.500	0.201	0.217
D2	4.250	4.450	0.167	0.175
e	1.270 BSC.		0.050 BSC.	
E	5.700	5.800	0.224	0.228
E1	6.000	6.300	0.236	0.248
E2	3.570	3.770	0.141	0.148
F	1.180	1.380	0.046	0.054
L	0.550	0.750	0.022	0.030
L1	0.150	0.250	0.006	0.010
L2	0.450	0.650	0.018	0.026
φ	0.900	1.100	0.035	0.043
θ	8°	12°	8°	12°